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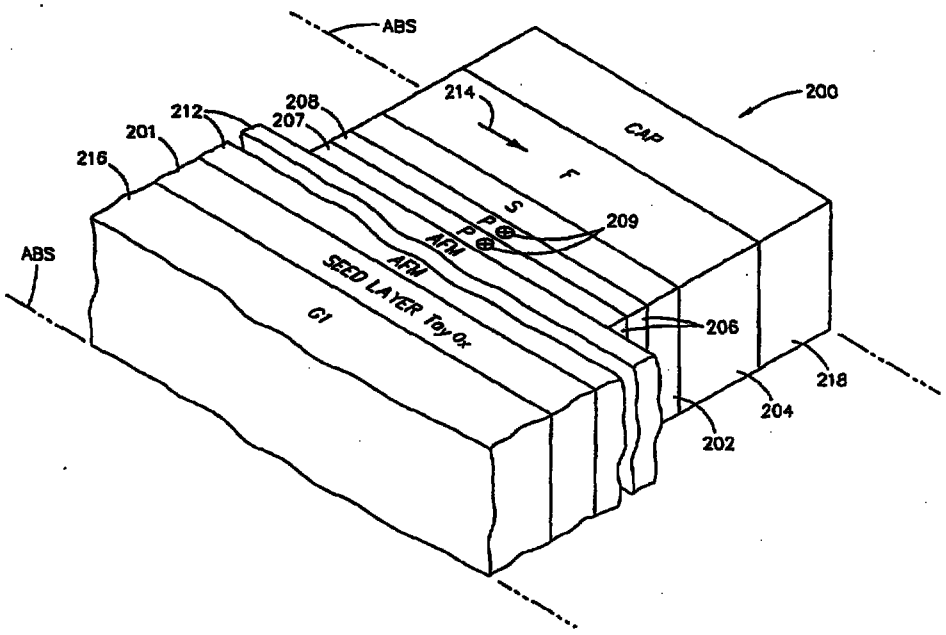
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(54) Title: SEED LAYER FOR A NICKEL OXIDE PINNING LAYER FOR INCREASING THE MAGNETORESISTANCE OF A SPIN VALVE SENSOR



(57) Abstract

A bottom spin valve sensor employs a seed layer (201) for a nickel oxide (NiO) antiferromagnetic pinning layer (212) for the purpose of increasing magnetoresistance of the sensor (dR/R). The spin valve sensor can be a simple spin valve or an antiparallel (AP) spin valve sensor. The seed layer is tantalum oxide $Ta^{y}O_{x}$ or copper (Cu).